Client Reference No. 068736.0236 PATENT

PTO-1449 Information Disclosure Citation in an Application	Application No.	Applicant(s): GORDON MA ET AL.	
	Docket Number: 068736.0236	Group Art Unit:	Filing Date: February 27, 2004

U.S. PATENT DOCUMENTS

		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
PC	1	4,811,075	03/07/89	Eklund	357	46	04/24/87
PC	2	5,155,563	10/13/92	Davies et al.	357	23.4	03/18/91
PC	3	5,252,848	10/12/93	Adler et al.	257	328	02/03/92
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PC	5	6,168,983	01/02/01	Rumennik et al.	438	188	02/05/99
PC	6	6,563,171	05/13/03	Disney	257	342	11/12/02

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

NON-PATENT DOCUMENTS

		DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
PC	7	J.A. Appels and H.M.J. Vaes, "High voltage thin layer devices (RESURF devices)", IEDM technical digest, pp. 238-241	1979
PC	8	H.M.J. Vaes and J.A. Appels, "High voltage high current lateral devices", IEDM technical digest, pp. 87-90	1980
PC	9	T. Fujihira, "Theory of Semiconductor Superjunction Devices", Jpn. J. Appl. Phys., vol. 36, pp. pp. 6254-6262	1997
PC	10	G. Deboy, et al., "A new generation of high voltage MOSFETs breaks the limit line of silicon", IEDM technical digest, pp. 683-685	1998
PC	11	A. Ludikhuize, "A review of RESURF technology", Proc. of ISPSD, p. 11	2000
PC	12	J. Cai, et al., "A novel high performance stacked LDD RF LDMOSFET, IEEE Electron Device Lett., vol. 22, no. 5, pp. 236-238	2001
PC	13	J.G. Mena and C.A.T. Salama, "High voltage multiple-resistivity Drift-Region LDMOS", Solid State Electronics, Vol. 29, No. 6, pp. 647-656	1986
PC	14	M.D. Pocha and R.W. Dutton, "A computer-aided design model for High-Voltage Double Diffused MOS (DMOS) Transistors", IEEE Journal of Solid-State Circuits, Vol. SC-11, No. 5	1976
PC	15	I. Yoshia, et al.; "Highly Efficient 1.5 GHz Si Power MOSFET for Digital Cellular Front End"; Proceedings of International Symposium on Power Semiconductor Devices & ICs; Tokyo, pp. 156-157	1992
PC	16	Helmut Brech et al; "Record Efficiency and Gain at 2.1 GHz of Hih Power RF Transistors for Cellular and 3G Base Stations"; RF & DSP INfrastructure Devision, Semiconductor Products Sector, Motorola, Tempe, Arizona	2003

EXAMINER	DATE CONSIDERED
PHAT X. CAO	2/10/06

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.